



ISO742x 低功耗双通道数字隔离器

1 特性

- 信号传输速率 > 50Mbps
- 默认输出“高”和“低”选项
- 低功耗：每通道 I_{CC} 典型值（3.3V 电源）：
 - ISO7420：1Mbps 下为 1.4mA，25Mbps 下为 2.5mA
 - ISO7421：1Mbps 下为 1.8mA，25Mbps 下为 2.8mA
- 低传播延迟：7ns，典型值
- 低脉冲偏移：200ps，典型值
- 宽 T_A 额定范围：-40°C 至 125°C
- 50kV/ μ s 瞬态抗扰度，典型值
- 隔离栅寿命：> 25 年
- 由 3V 至 5.5V 电源电平供电
- 3.3V 和 5V 电平转换
- 窄体小尺寸集成电路 (SOIC)-8 封装
- 安全及管理批准：
 - 符合 DIN V VDE V 0884-10 和 DIN EN 61010-1 标准的 4242 V_{PK} 隔离
 - 符合 UL 1577 标准且长达 1 分钟的 2500 V_{RMS} 隔离
 - CSA 组件接受通知 5A，IEC 60950-1 和 IEC 61010-1 标准
 - 符合 GB4943.1-2011 的 CQC 认证

2 应用

- 在下列使用中的光电耦合器替代产品：
 - 工业用 FieldBus
 - ProfiBus
 - ModBus
 - DeviceNet™ 数据总线
 - 伺服控制接口
 - 电机控制
 - 电源
 - 电池组

3 说明

ISO742x 可提供符合 UL 标准的长达 1 分钟且高达 2500V_{RMS} 的电流隔离，以及符合 VDE 标准的 4242V_{PK} 隔离。这些器件有 2 个隔离通道。每个通道有一个逻辑输入和输出缓冲器，这两个器件由一个硅二极管(SiO₂) 绝缘栅进行分离。通过与隔离电源一起使用，这些器件可防止数据总线或者其它电路上的噪声电流进入本地接地并干扰或者损坏敏感电路。ISO7420 的两个通道方向相同，而 ISO7421 的两个通道方向相反。如果出现输入功率或信号损失，则后缀为“F”的器件默认输出“低”电平，后缀没有“F”的器件则默认输出“高”电平。ISO742x 未集成噪声滤波器，因而传播延迟相对短暂。

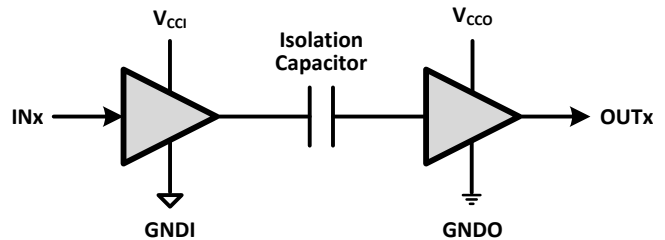
这些器件具有晶体管晶体管逻辑电路 (TTL) 输入阈值，工作电压范围为 3V 到 5.5V。当由一个 3.3V 电源供电时，所有输入均为 5V 耐压。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
ISO7420E	SOIC (8)	4.90mm x 3.91mm
ISO7420FE		
ISO7421E		
ISO7421FE		

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



V_{CCI} 和 $GNDI$ 分别是输入通道的电源和接地连接。

V_{CCO} 和 $GNDO$ 分别是输出通道的电源和接地连接。



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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision E (January 2013) to Revision F	Page
• 已根据最新的 TI 标准更改数据表格式	1
• 已添加 引脚配置和功能部分, ESD 额定值表, 特性 描述 部分, 器件功能模式, 应用和 实施部分, 电源相关建议部分, 布局部分, 器件和文档支持部分以及 机械、封装和可订购信息部分	1
• 已删除 说明部分的如下文本: “CC 级器件集成有应用于恶劣环境的 10ns 滤波器, 在这种环境下, 器件的输入引脚上可能存在短噪声脉冲。”	1
• VDE 标准更改为 DIN V VDE V 0884-10 (VDE V 0884-10):2006-12	1
• Deleted CC-grade from t_{PLH} , t_{PHL} in the Switching Characteristics table	10
• Deleted CC-grade from t_{PLH} , t_{PHL} in the Switching Characteristics table	10
• Deleted CC-grade from t_{PLH} , t_{PHL} in the Switching Characteristics table	11
• Deleted CC-grade from t_{PLH} , t_{PHL} in the Switching Characteristics table	11
• Changed the Available Options Table To the Feature Description table	17

Changes from Revision D (December 2011) to Revision E	Page
• 已删除器件 ISO7420FCC 和 ISO7421FCC	1
• Changed the NOTE: text	17
• Added table Note to V_{IORM}	18
• Changed Z to Undetermined for the OUTPUT OUTA, OUTB column of the FUNCTION TABLE	20

Changes from Revision C (March 2011) to Revision D
Page

• 已将安全特性要点从“已通过 UL 1577 审批；其他审批正在审理中”更改为“所有机构的审批已通过”	1
• Changed the REGULATORY INFORMATION table	18

Changes from Revision B (January 2011) to Revision C
Page

• 已添加器件 ISO7420FCC 和 ISO7421FCC	1
• 已将特性要点更改为：低传播延迟：7ns，典型值（E 级）	1
• 已将特性要点更改为：低脉冲偏移：200ps，典型值（E 级）	1
• 已更改安全及管理批准列表	1
• 已更改数据表 说明	1
• Changed the Supply Current values for ISO7421x at 10, 25, and 50 Mbps	6
• Changed the Supply Current values for ISO7421x at 10, 25, and 50 Mbps	7
• Changed the Supply Current values for ISO7421x at 10, 25, and 50 Mbps	8
• Changed the Supply Current values for ISO7421x 25 and 50 Mbps	9
• Added CC-grade and valued to t_{PLH} , t_{PHL} in the Switching Characteristics table	10
• Added ISO7421x values for Pulse width distortion, Channel-to-channel output skew time, and Part-to-part skew time	10
• Added CC-grade and valued to t_{PLH} , t_{PHL} in the Switching Characteristics table	10
• Added ISO7421x values for Pulse width distortion and Channel-to-channel output skew time	10
• Added CC-grade and valued to t_{PLH} , t_{PHL} in the Switching Characteristics table	11
• Added CC-grade and valued to t_{PLH} , t_{PHL} in the Switching Characteristics table	11
• Added graphs Figure 5 , Figure 6 , Figure 7 , and Figure 8	12
• Added graphs Figure 14 and Figure 15	13
• Changed Note 1 Figure 16	15
• Changed Figure 17	15
• Changed the Available Options Table	17
• Changed Isolation resistance test conditions	17
• Changed the values of V_{IORM} and V_{PR} in the INSULATION CHARACTERISTICS table	18
• Changed the value of V_{IOTM} in the INSULATION CHARACTERISTICS table From: 4000 To: 4242	18
• Changed Figure 21	19
• Changed PU to X in the last row of the FUNCTION TABLE	20
• Added section: SUPPLY CURRENT EQUATIONS	22

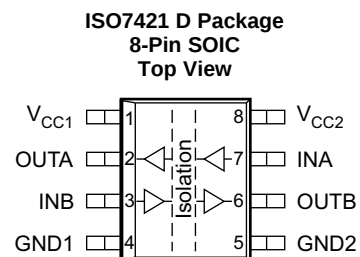
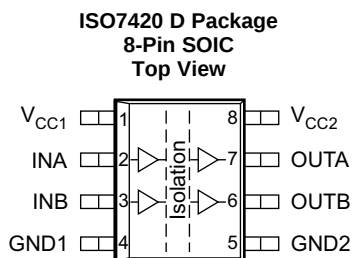
Changes from Revision A (December 2010) to Revision B
Page

• 将特性着重号从：ISO7421:1Mbps下为TBDmA，25Mbps下为TBDmA改到：ISO7421：1Mbps下为1.8mA，25Mbps下为2.8mA	1
• Updated the ISO7421x Supply Current values for V_{CC1} and $V_{CC2} = 5V$	6
• Updated the ISO7421x Supply Current values for $V_{CC1} = 5V$ and $V_{CC2} = 3.3V$	7
• Updated the ISO7421x Supply Current values for $V_{CC1} = 3.3V$ and $V_{CC2} = 5V$	8
• Updated the ISO7421x Supply Current values for V_{CC1} and $V_{CC2} = 3.3V$	9

Changes from Original (December 2010) to Revision A
Page

• Changed the Max values for Supply current for V_{CC1} and V_{CC2} , $C_L = 15pF$	9
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5 Pin Configuration and Functions



Pin Functions

NAME	PIN		I/O	DESCRIPTION
	ISO7420x	ISO7421x		
INA	2	7	I	Input, channel A
INB	3	3	I	Input, channel B
GND1	4	4	–	Ground connection for V _{CC1}
GND2	5	5	–	Ground connection for V _{CC2}
OUTA	7	2	O	Output, channel A
OUTB	6	6	O	Output, channel B
V _{CC1}	1	1	–	Power supply, V _{CC1}
V _{CC2}	8	8	–	Power supply, V _{CC2}

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾ , V _{CC1} , V _{CC2}	−0.5	6	V
V _I	Voltage at IN, OUT	−0.5	V _{CC} + 0.5 ⁽³⁾	V
I _O	Output current		±15	mA
V _{SRG}	Maximum surge immunity - Supports IEC 61000-4-5		4000	V _{PK}
T _{J(Max)}	Maximum junction temperature		150	°C
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground terminal and are peak voltage values.
- (3) Maximum voltage must not exceed 6 V.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge		
	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±3000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	
	Machine model (MM) ANSI/ESDS5.2-1996	±200	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V _{CC1} , V _{CC2}	Supply voltage	3.0		5.5	V
I _{OH}	High-level output current	−4			mA
I _{OL}	Low-level output current			4	mA
V _{IH}	High-level input voltage	2		5.5	V
V _{IL}	Low-level input voltage	0		0.8	V
t _{ui}	Input pulse duration	20			ns
1 / t _{ui}	Signaling rate	0		50 ⁽¹⁾	Mbps
T _J ⁽²⁾	Junction temperature	−40		136	°C
T _A	Ambient Temperature	−40	25	125	°C

- (1) Under typical conditions, these devices are capable of signaling rate > 150 Mbps.
- (2) To maintain the recommended operating conditions for T_J, see the [Thermal Information](#) table.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾			ISO742x	UNIT
			D (SOIC)	
			8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	Low-K board	212	°C/W
		High-K board	116.6	
R _{θJC(top)}	Junction-to-case (top) thermal resistance		71.6	°C/W
R _{θJB}	Junction-to-board thermal resistance		57.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter		28.3	°C/W
ψ _{JB}	Junction-to-board characterization parameter		56.8	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics: V_{CC1} and $V_{CC2} = 5\text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
V _{OH}	High-level output voltage	I _{OH} = −4 mA; see Figure 16 .		V _{CCO} ⁽¹⁾ − 0.8	4.6		V	
		I _{OH} = −20 μA; see Figure 16 .		V _{CCO} − 0.1	5			
V _{OL}	Low-level output voltage	I _{OL} = 4 mA; see Figure 16 .			0.2	0.4	V	
		I _{OL} = 20 μA; see Figure 16 .			0	0.1		
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV	
I _{IH}	High-level input current	I _{Nx} at 0 V or V _{CCI} ⁽¹⁾				10	μA	
I _{IL}	Low-level input current			−10			μA	
CMTI	Common-mode transient immunity	V _I = V _{CCI} or 0 V; see Figure 18 .		25	50		kV/μs	
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC I _{CC} MEASUREMENT)								
ISO7420x								
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CCI} or 0 V, AC Input: C _L = 15 pF			0.4	0.8	mA
I _{CC2}						3.4	5	
I _{CC1}		10 Mbps	C _L = 15 pF			0.6	1	
I _{CC2}						4.5	6	
I _{CC1}		25 Mbps				1	1.5	
I _{CC2}						6.2	8	
I _{CC1}		50 Mbps				1.7	2.5	
I _{CC2}						9	12	
ISO7421x								
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CCI} or 0 V, AC Input: C _L = 15 pF			2.3	3.6	mA
I _{CC2}						2.3	3.6	
I _{CC1}		10 Mbps	C _L = 15 pF			2.9	4.5	
I _{CC2}						2.9	4.5	
I _{CC1}		25 Mbps				4.3	6	
I _{CC2}						4.3	6	
I _{CC1}		50 Mbps				6	8.5	
I _{CC2}						6	8.5	

 (1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC}

6.6 Electrical Characteristics: $V_{CC1} = 5\text{ V} \pm 10\%$, $V_{CC2} = 3.3\text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = −4 mA; see Figure 16.	ISO7421x (5-V side)	V _{CC1} − 0.8	4.6		V
			ISO7420x/7421x (3.3-V side)	V _{CC2} − 0.4	3		
		I _{OH} = −20 μA; see Figure 16.	ISO7421x (5-V side)	V _{CC1} − 0.1	5		
			ISO7420x/7421x (3.3-V side)	V _{CC2} − 0.1	3.3		
V _{OL}	Low-level output voltage	I _{OL} = 4 mA; see Figure 16.			0.2	0.4	V
		I _{OL} = 20 μA; see Figure 16.			0	0.1	
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	INx at 0 V or V _{CC1}				10	μA
I _{IL}	Low-level input current			−10			μA
CMTI	Common-mode transient immunity	V _I = V _{CC1} or 0 V; see Figure 18.		25	50		kV/μs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC I _{CC} MEASUREMENT)							
ISO7420x							
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CC1} or 0 V, AC Input: C _L = 15 pF		0.4	0.8	mA
I _{CC2}					2.6	3.7	
I _{CC1}		10 Mbps	C _L = 15 pF		0.6	1	
I _{CC2}					3.3	4.3	
I _{CC1}		25 Mbps			1	1.5	
I _{CC2}					4.4	5.6	
I _{CC1}		50 Mbps			1.7	2.5	
I _{CC2}					6.2	7.5	
ISO7421x							
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CC1} or 0 V, AC Input: C _L = 15 pF		2.3	3.6	mA
I _{CC2}					1.8	2.8	
I _{CC1}		10 Mbps	C _L = 15 pF		2.9	4.5	
I _{CC2}					2.2	3.2	
I _{CC1}		25 Mbps			4.3	6	
I _{CC2}					2.8	4.1	
I _{CC1}		50 Mbps			6	8.5	
I _{CC2}					3.8	5.5	

6.7 Electrical Characteristics: $V_{CC1} = 3.3 \text{ V} \pm 10\%$, $V_{CC2} = 5 \text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = −4 mA; see Figure 16.	ISO7421x (3.3-V side)	V _{CC1} − 0.4	3		V
			ISO7420x/7421x (5-V side)	V _{CC2} − 0.8	4.6		
		I _{OH} = −20 μA; see Figure 16	ISO7421x (3.3-V side)	V _{CC1} − 0.1	3.3		
			ISO7420x/7421x (5-V side)	V _{CC2} − 0.1	5		
V _{OL}	Low-level output voltage	I _{OL} = 4 mA; see Figure 16.			0.2	0.4	V
		I _{OL} = 20 μA; see Figure 16.			0	0.1	
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	INx at 0 V or V _{CCI}				10	μA
I _{IL}	Low-level input current				−10		μA
CMTI	Common-mode transient immunity	V _I = V _{CCI} or 0 V; see Figure 18.		25	50		kV/μs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC I _{CC} MEASUREMENT)							
ISO7420x							
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CCI} or 0 V, AC Input: C _L = 15 pF		0.2	0.4	mA
I _{CC2}					3.4	5	
I _{CC1}		10 Mbps	C _L = 15 pF		0.4	0.6	
I _{CC2}					4.5	6	
I _{CC1}		25 Mbps			0.6	0.9	
I _{CC2}					6.2	8	
I _{CC1}		50 Mbps			1	1.3	
I _{CC2}					9	12	
ISO7421x							
I _{CC1}	Supply current for V _{CC2} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CCI} or 0 V, AC Input: C _L = 15 pF		1.8	2.8	mA
I _{CC2}					2.3	3.6	
I _{CC1}		10 Mbps	C _L = 15 pF		2.2	3.2	
I _{CC2}					2.9	4.5	
I _{CC1}		25 Mbps			2.8	4.1	
I _{CC2}					4.3	6	
I _{CC1}		50 Mbps			3.8	5.5	
I _{CC2}					6	8.5	

6.8 Electrical Characteristics: V_{CC1} and $V_{CC2} = 3.3 \text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = −4 mA; see Figure 16 .		V _{CCO} ⁽¹⁾ − 0.4	3		V
		I _{OH} = −20 μA; see Figure 16 .		V _{CCO} − 0.1	3.3		
V _{OL}	Low-level output voltage	I _{OL} = 4 mA; see Figure 16 .			0.2	0.4	V
		I _{OL} = 20 μA; see Figure 16 .			0	0.1	
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	INx at 0 V or V _{CCI} ⁽¹⁾				10	μA
I _{IL}	Low-level input current				−10		μA
CMTI	Common-mode transient immunity	V _I = V _{CCI} or 0 V; see Figure 18 .		25	50		kV/μs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC I _{CC} MEASUREMENT)							
ISO7420x							
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CCI} or 0 V, AC Input: C _L = 15 pF		0.2	0.4	mA
I _{CC2}					2.6	3.7	
I _{CC1}		10 Mbps	C _L = 15 pF		0.4	0.6	
I _{CC2}					3.3	4.3	
I _{CC1}		25 Mbps			0.6	0.9	
I _{CC2}					4.4	5.6	
I _{CC1}		50 Mbps			1	1.3	
I _{CC2}					6.2	7.5	
ISO7421x							
I _{CC1}	Supply current for V _{CC2} and V _{CC2}	DC to 1 Mbps	DC Input: V _I = V _{CCI} or 0 V, AC Input: C _L = 15 pF		1.8	2.8	mA
I _{CC2}					1.8	2.8	
I _{CC1}		10 Mbps	C _L = 15 pF		2.2	3.2	
I _{CC2}					2.2	3.2	
I _{CC1}		25 Mbps			2.8	4.1	
I _{CC2}					2.8	4.1	
I _{CC1}		50 Mbps			3.8	5.5	
I _{CC2}					3.8	5.5	

(1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC}

6.9 Power Dissipation Characteristics

THERMAL METRIC			ISO742x	UNIT
			D (SOIC)	
			8 PINS	
P _D	Device power dissipation	V _{CC1} = V _{CC2} = 5.5 V, T _J = 150°C, C _L = 15 pF, Input a 100-Mbps 50% duty-cycle square wave	138	mW

6.10 Switching Characteristics: V_{CC1} and $V_{CC2} = 5\text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time		See Figure 16.	7	11		ns
PWD ⁽¹⁾	Pulse width distortion t _{PHL} – t _{PLH}	ISO7420x		0.2	3		ns
		ISO7421x		0.3	3.7		
t _{sk(o)} ⁽²⁾	Channel-to-channel output skew time	ISO7420x		0.3	1		ns
		ISO7421x		0.3	2		
t _{sk(pp)} ⁽³⁾	Part-to-part skew time	ISO7420x			3.7		ns
		ISO7421x			4.9		
t _r	Output signal rise time		See Figure 16.	1.8			ns
t _f	Output signal fall time			1.7			ns
t _{fs}	Fail-safe output delay time from input power loss		See Figure 17.	6			μs

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

6.11 Switching Characteristics: $V_{CC1} = 5\text{ V} \pm 10\%$, $V_{CC2} = 3.3\text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time		See Figure 16 .	8	13.5		ns
PWD ⁽¹⁾	Pulse width distortion t _{PHL} – t _{PLH}	ISO7420x		0.3	3		ns
		ISO7421x		0.5	5.6		
t _{sk(o)} ⁽²⁾	Channel-to-channel output skew time	ISO7420x				1.5	ns
		ISO7421x		0.5	3		
t _{sk(pp)} ⁽³⁾	Part-to-part skew time	ISO7420x				5.4	ns
		ISO7421x				6.3	
t _r	Output signal rise time		See Figure 16 .	2			ns
t _f	Output signal fall time			2			ns
t _{is}	Fail-safe output delay time from input power loss		See Figure 17 .	6			μs

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

6.12 Switching Characteristics: $V_{CC1} = 3.3\text{ V} \pm 10\%$, $V_{CC2} = 5\text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 16.		7.5	12	ns
				7.5	14	
PWD ⁽¹⁾	Pulse width distortion $ t_{PHL} - t_{PLH} $			0.7	3	ns
				0.7	3.6	
$t_{sk(o)}$ ⁽²⁾	Channel-to-channel output skew time			0.5	1.5	ns
				0.5	3	
$t_{sk(pp)}$ ⁽³⁾	Part-to-part skew time				4.6	ns
					8.5	
t_r	Output signal rise time	See Figure 16.		1.7		ns
t_f	Output signal fall time			1.6		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 17.		6		μs

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

6.13 Switching Characteristics: V_{CC1} and $V_{CC2} = 3.3\text{ V} \pm 10\%$

 $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 16		8.5	14	ns
PWD ⁽¹⁾	Pulse width distortion $ t_{PHL} - t_{PLH} $			0.5	2	ns
$t_{sk(o)}$ ⁽²⁾	Channel-to-channel output skew time			0.4	2	ns
				0.4	3	
$t_{sk(pp)}$ ⁽³⁾	Part-to-part skew time				6.2	ns
					6.8	
t_r	Output signal rise time	See Figure 16		2		ns
t_f	Output signal fall time			1.8		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 17		6		μs

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

6.14 Typical Characteristics

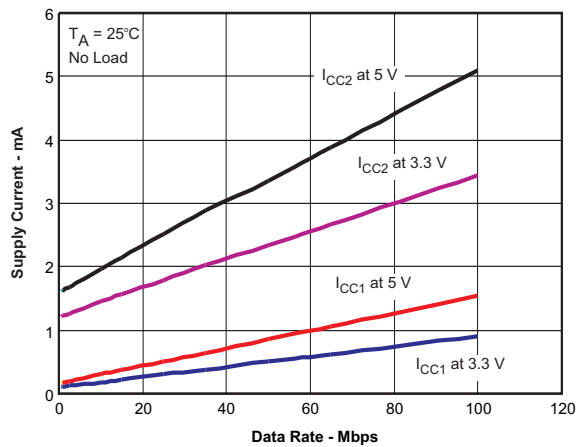


Figure 1. ISO7420 Supply Current Per Channel vs Data Rate (No Load)

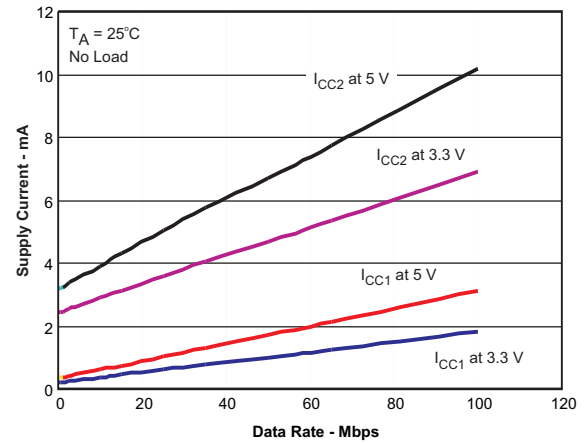


Figure 2. ISO7420 Supply Current Both Channels vs Data Rate (No Load)

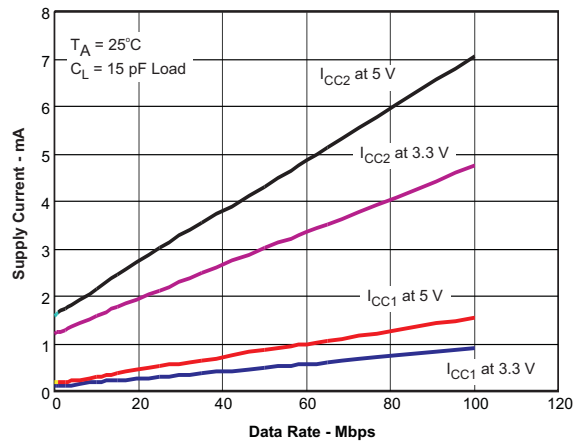


Figure 3. ISO7420 Supply Current Per Channel vs Data Rate (15 pF Load)

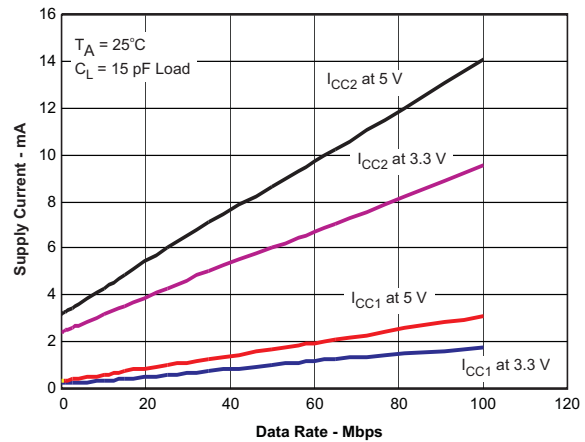


Figure 4. ISO7420 Supply Current Both Channels vs Data Rate (15 pF Load)

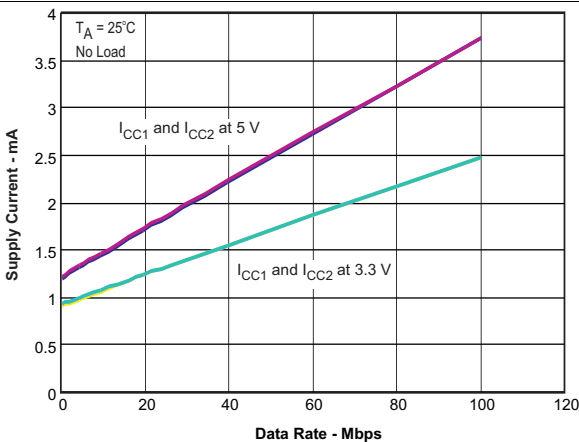


Figure 5. ISO7421 Supply Current Per Channel vs Data Rate (No Load)

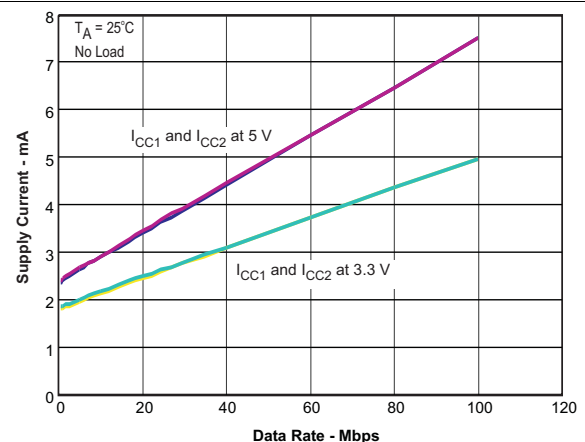


Figure 6. ISO7421 Supply Current Both Channels vs Data Rate (No Load)

Typical Characteristics (continued)

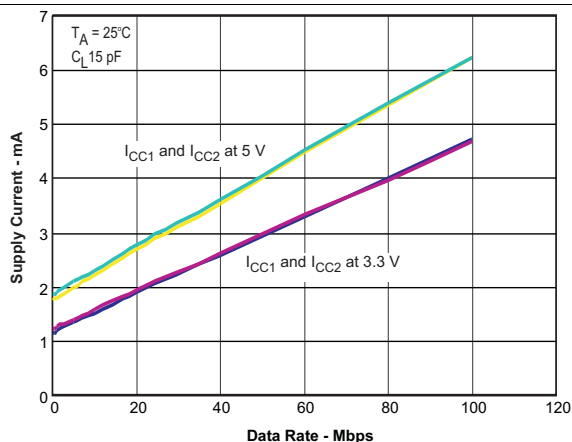


Figure 7. ISO7421 Supply Current Per Channel vs Data Rate (15 pF Load)

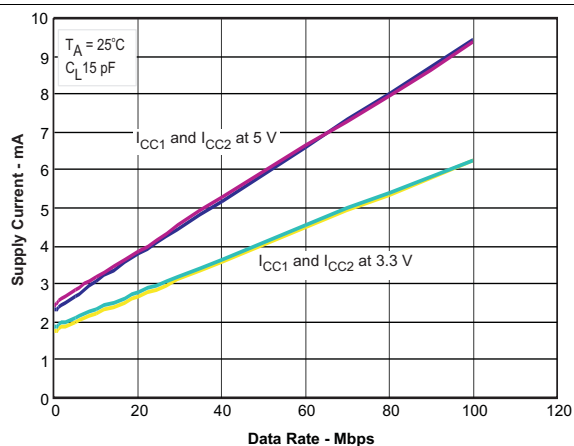


Figure 8. ISO7421 Supply Current Both Channels vs Data Rate (15 pF Load)

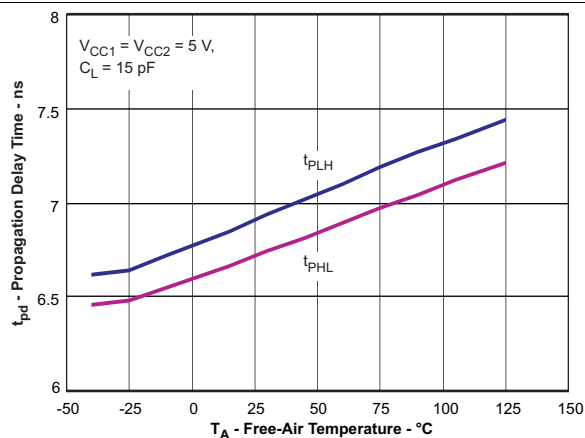


Figure 9. Propagation Delay Time vs Free-Air Temperature

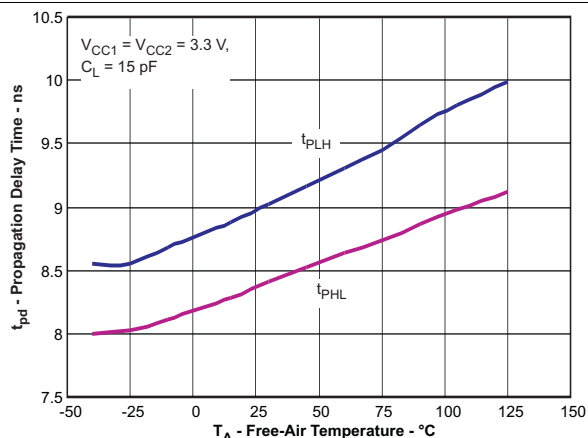


Figure 10. Propagation Delay Time vs Free-Air Temperature

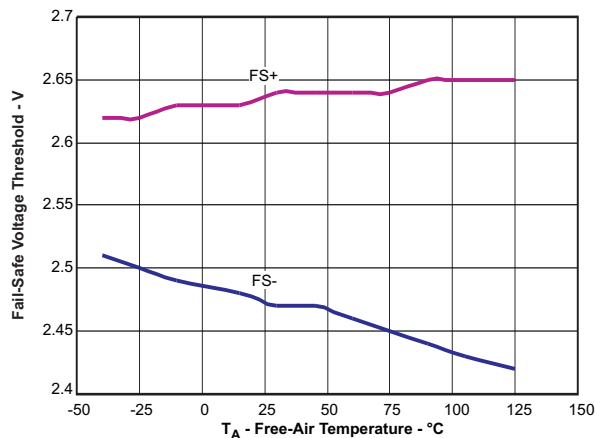


Figure 11. Input V_{CC} Fail-Safe Voltage Threshold vs Free-Air Temperature

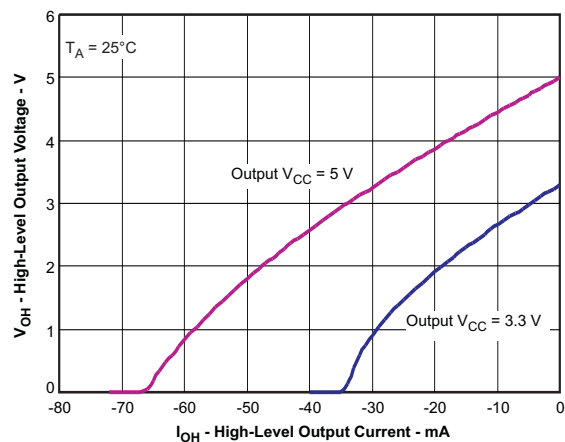


Figure 12. High-Level Output Voltage vs High-Level Output Current

Typical Characteristics (continued)

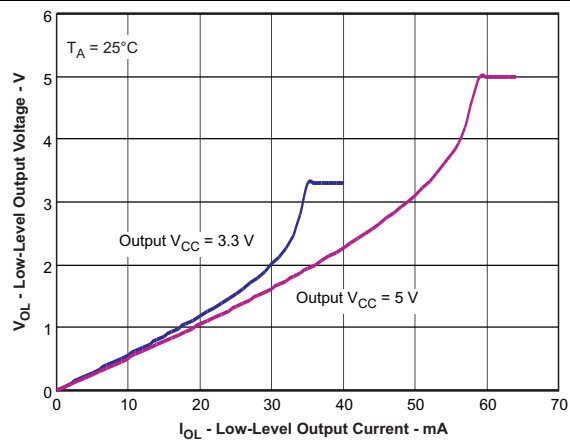


Figure 13. Low-Level Output Voltage vs Low-Level Output Current

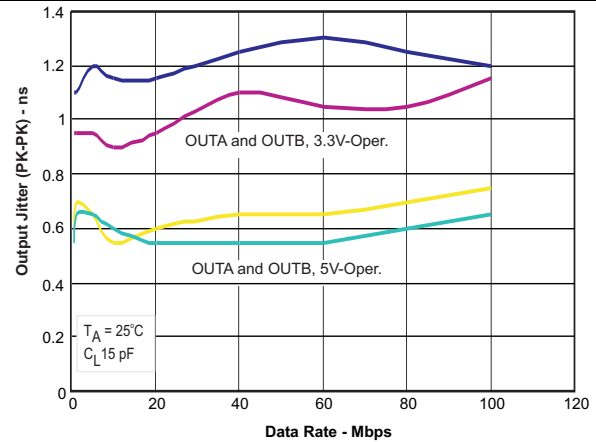


Figure 14. ISO7420FE Output Jitter vs Data Rate

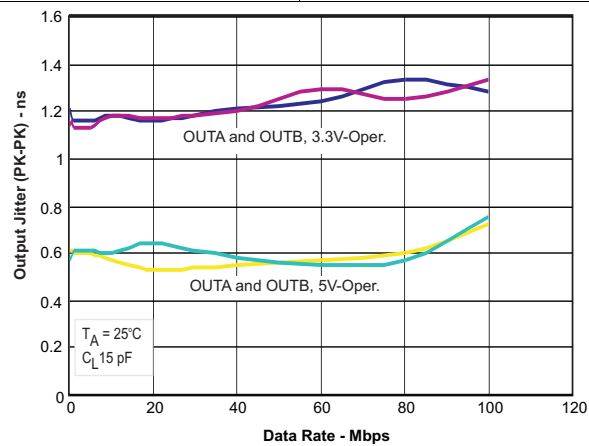
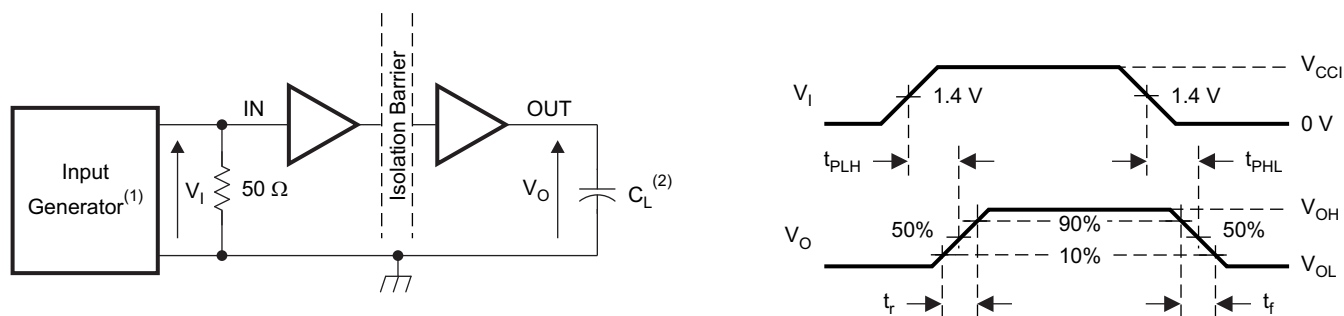


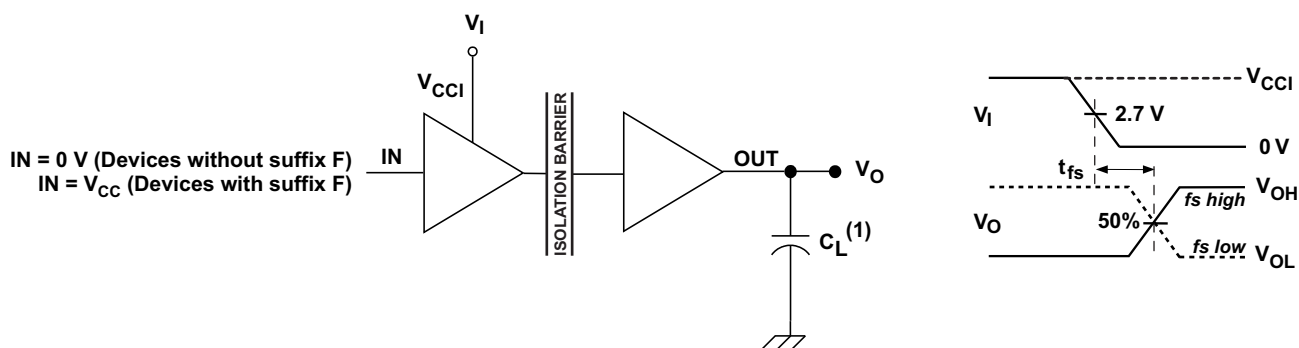
Figure 15. ISO7421FE Output Jitter vs Data Rate

7 Parameter Measurement Information



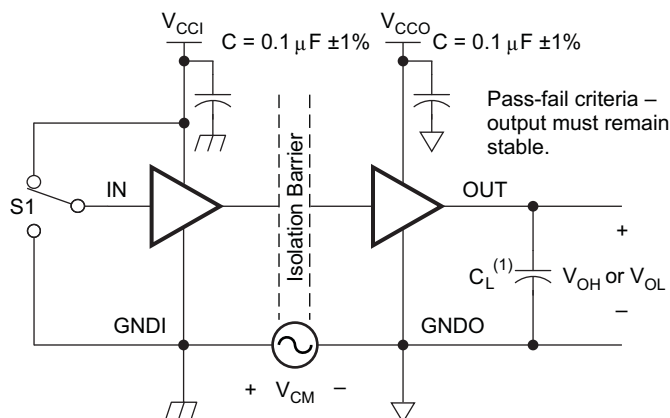
- (1) The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_O = 50 \Omega$. At the input, a 50-Ω resistor is required to terminate the Input Generator signal. It is not needed in an actual application.
- (2) $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 16. Switching Characteristic Test Circuit and Voltage Waveforms



- (1) $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 17. Fail-Safe Output Delay-Time Test Circuit and Voltage Waveforms



- (1) $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 18. Common-Mode Transient Immunity Test Circuit

8 Detailed Description

8.1 Overview

The isolator in Figure 19 is based on a capacitive isolation barrier technique. The I/O channel of the device consists of two internal data channels, a high-frequency channel (HF) with a bandwidth from 100 kbps up to 150 Mbps, and a low-frequency channel (LF) covering the range from 100 kbps down to DC. In principle, a single-ended input signal entering the HF-channel is split into a differential signal via the inverter gate at the input. The following capacitor-resistor networks differentiate the signal into transients, which then are converted into differential pulses by two comparators. The comparator outputs drive a NOR-gate flip-flop whose output feeds an output multiplexer. A decision logic (DCL) at the driving output of the flip-flop measures the durations between signal transients. If the duration between two consecutive transients exceeds a certain time limit, (as in the case of a low-frequency signal), the DCL forces the output-multiplexer to switch from the high- to the low-frequency channel.

Because low-frequency input signals require the internal capacitors to assume prohibitively large values, these signals are pulse-width modulated (PWM) with the carrier frequency of an internal oscillator, thus creating a sufficiently high frequency signal, capable of passing the capacitive barrier. As the input is modulated, a low-pass filter (LPF) is needed to remove the high-frequency carrier from the actual data before passing it on to the output multiplexer.

8.2 Functional Block Diagram

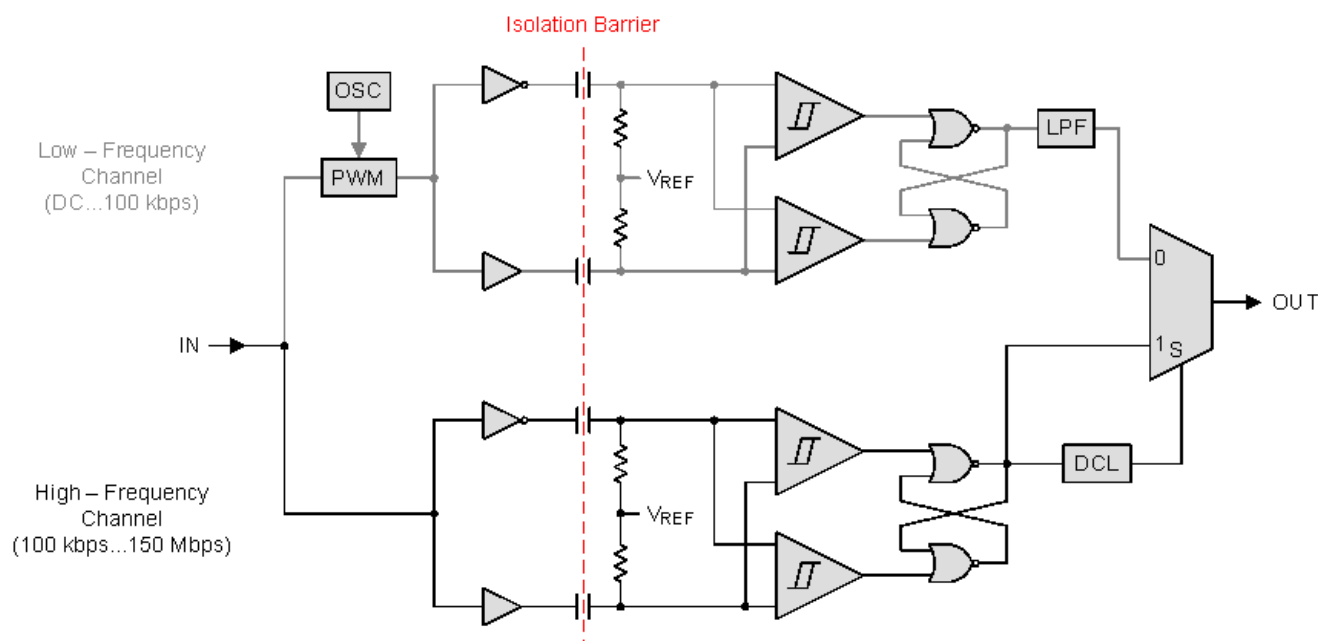


Figure 19. Conceptual Block Diagram of a Digital Capacitive Isolator

8.3 Feature Description

ISO742x are available in multiple channel configurations and default output state options to enable wide variety of application uses.

PRODUCT	DATA RATE	DEFAULT OUTPUT	RATED T_A	CHANNEL DIRECTION
ISO7420E	50 Mbps	High	–40°C to 125°C	Same
ISO7420FE		Low		
ISO7421E		High		Opposite
ISO7421FE		Low		

8.3.1 Insulation and Safety-Related Specifications for D-8 Package

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01) Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	4			mm
L(I02) Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	4			mm
CTI Tracking resistance (comparative tracking index)	DIN EN 60112 (VDE 0303-11); IEC 60112	>400			V
Minimum internal gap (internal clearance)	Distance through the insulation	0.014			mm
R_{IO} Isolation resistance, input to output ⁽¹⁾	$V_{IO} = 500\text{ V}$, $T_A = 25^\circ\text{C}$	>10 ¹²			Ω
	$V_{IO} = 500\text{ V}$, $100^\circ\text{C} \leq T_A \leq \text{max}$	>10 ¹¹			Ω
C_{IO} Barrier capacitance, input to output ⁽¹⁾	$V_{IO} = 0.4 \sin(2\pi ft)$, $f = 1\text{ MHz}$		1		pF
C_I Input capacitance ⁽²⁾	$V_I = V_{CC}/2 + 0.4 \sin(2\pi ft)$, $f = 1\text{ MHz}$, $V_{CC} = 5\text{ V}$		1		pF

(1) All pins on each side of the barrier tied together creating a two-terminal device.

(2) Measured from input pin to ground.

NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

8.3.2 Insulation Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER ⁽¹⁾		TEST CONDITIONS	SPECIFICATION	UNIT
DIN V VDE V 0884-10 (VDE V 0884-10):2006-12				
V _{IORM}	Maximum working isolation voltage		566	V _{PEAK}
V _{PR}	Input-to-output test voltage	Method a, After environmental tests subgroup 1, V _{PR} = V _{IORM} × 1.6, t = 10 s, Partial Discharge < 5 pC	906	V _{PEAK}
		Method b1, V _{PR} = V _{IORM} × 1.875, t = 1 s (100% Production test) Partial discharge < 5 pC	1062	
		After Input/Output safety test subgroup 2/3, V _{PR} = V _{IORM} × 1.2, t = 10 s, Partial discharge < 5 pC	680	
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} = 4242 V _{PK} t = 60 sec (qualification) t = 1 sec (100% production)	4242	V _{PEAK}
R _S	Isolation resistance	V _{IO} = 500 V at T _S = 150°C	>10 ⁹	Ω
	Pollution degree		2	
UL 1577				
V _{ISO}	Maximum withstand isolation voltage	V _{TEST} = V _{ISO} = 2500 V _{RMS} , t = 60 sec (qualification); V _{TEST} = 1.2 × V _{ISO} = 3000 V _{RMS} , t = 1 sec (100% production)	2500	V _{RMS}

(1) Climatic Classification 40/125/21

Table 1. IEC 60664-1 Ratings Table

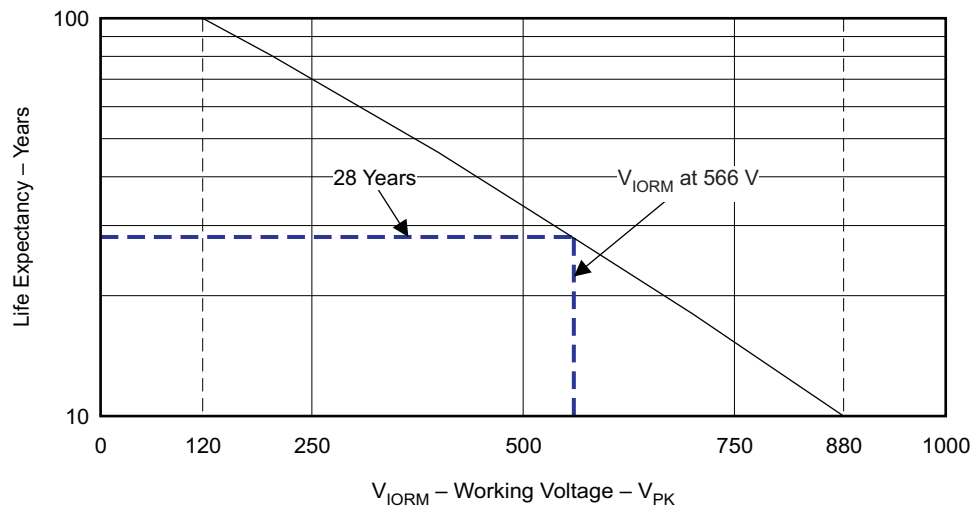
PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	II
Installation classification	Rated mains voltage ≤ 150 V _{RMS}	I–IV
	Rated mains voltage ≤ 300 V _{RMS}	I–III

8.3.3 Regulatory Information

VDE	CSA	UL	CQC
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 61010-1 (VDE 0411-1):2011-07	Approved under CSA Component Acceptance Notice 5A, IEC 60950-1, and IEC 61010-1	Recognized under UL 1577 Component Recognition Program	Certified according to GB 4943.1-2011
Basic Insulation; Maximum Transient Isolation Voltage, 4242 V _{PK} ; Maximum Working Isolation Voltage, 566 V _{PK}	2500 V _{RMS} Isolation Rating; Basic insulation per CSA 60950-1-07+A1 and IEC 60950-1 2nd Ed+A1, 384 V _{RMS} maximum working voltage; CSA 61010-1-04 and IEC 61010-1 2nd Ed, 300 V _{RMS} maximum working voltage for basic insulation and 150 V _{RMS} for reinforced insulation	Single Protection Isolation Voltage, 2500 V _{RMS} ⁽¹⁾	Basic Insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V _{RMS} maximum working voltage
Certificate number: 40016131	Master contract number: 220991	File number: E181974	Certificate number: CQC14001109540

 (1) Production tested ≥ 3000 V_{RMS} for 1 second in accordance with UL 1577.

8.3.4 Life Expectancy vs Working Voltage



G001

Figure 20. Life Expectancy vs Working Voltage

8.3.5 Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _S Safety input, output, or supply current	$\theta_{JA} = 212^{\circ}\text{C/W}$, $V_I = 5.5\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			107	mA
	$\theta_{JA} = 212^{\circ}\text{C/W}$, $V_I = 3.6\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			164	
T _S Maximum safety temperature				150	$^{\circ}\text{C}$

The safety-limiting constraint is the absolute-maximum junction temperature specified in the [Absolute Maximum Ratings^{\(1\)}](#) table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the [Thermal Information](#) table is that of a device installed in the JEDEC51-3, Low-Effective-Thermal-Conductivity Test Board for Leadless Surface-Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

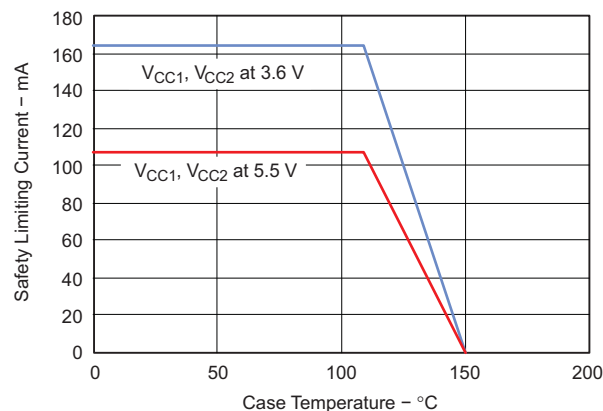


Figure 21. θ_{JC} Thermal Derating Curve per VDE

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

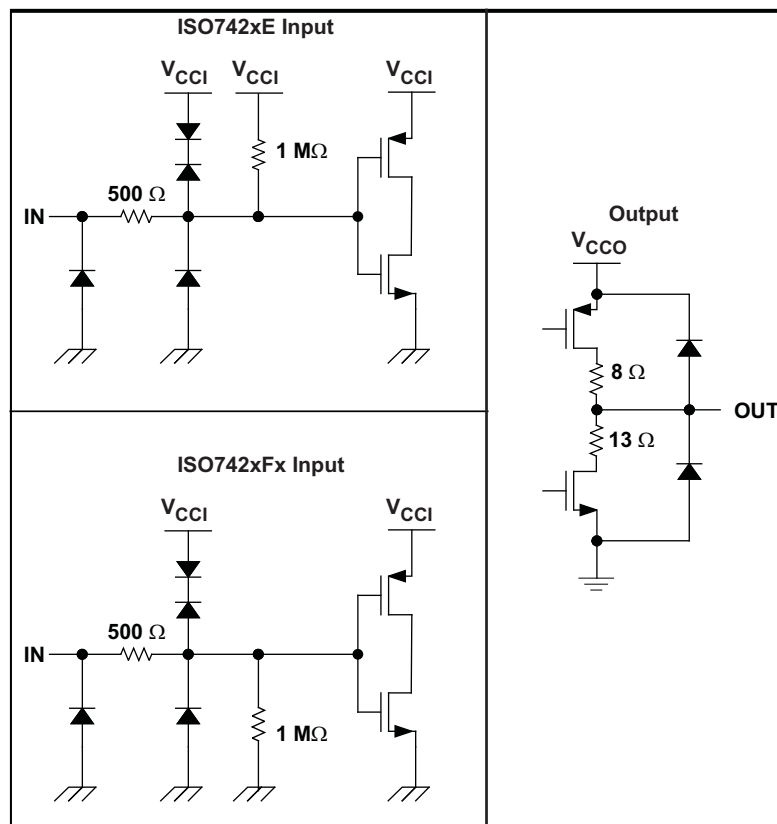
8.4 Device Functional Modes

Table 2. Functional Table⁽¹⁾

V_{CCI}	V_{CCO}	INPUT INA, INB	OUTPUT OUTA, OUTB	
			ISO7420E / ISO7421E	ISO7420FE / ISO7421FE
PU	PU	H	H	H
		L	L	L
		Open	H ⁽²⁾	L ⁽³⁾
PD	PU	X	H ⁽²⁾	L ⁽³⁾
X	PD	X	Undetermined	Undetermined

- (1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} ; PU = Powered up ($V_{CC} \geq 3$ V); PD = Powered down ($V_{CC} \leq 2.1$ V); X = Irrelevant; H = High level; L = Low level;
 (2) In fail-safe condition, output defaults to high level
 (3) In fail-safe condition, output defaults to low level

8.4.1 Device I/O Schematic


Figure 22. Device I/O Schematics

9 Applications and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

ISO742x utilize single-ended TTL-logic switching technology. Its supply voltage range is from 3 V to 5.5 V for both supplies, V_{CC1} and V_{CC2} . When designing with digital isolators, it is important to keep in mind that due to the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (i.e. μC or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

9.2 Typical Application

ISO7421 can be used with Texas Instruments' mixed signal micro-controller, digital-to-analog converter, transformer driver, and voltage regulator to create an isolated 4-20 mA current loop.

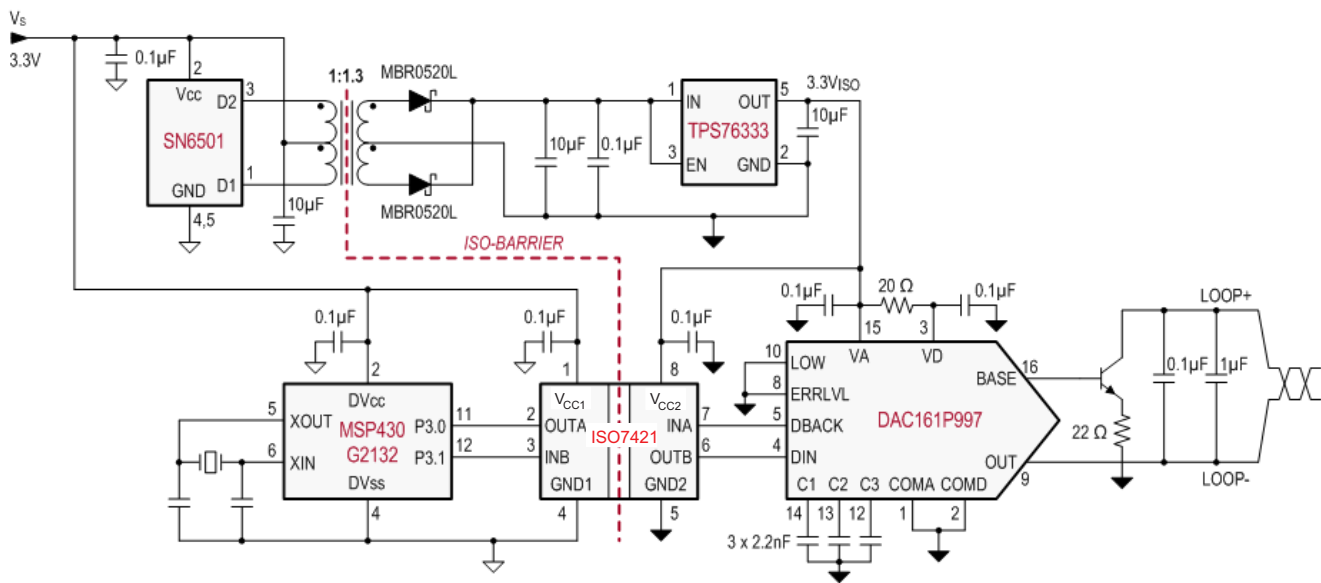


Figure 23. Isolated 4-20 mA Current Loop

Typical Application (continued)

9.2.1 Design Requirements

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the ISO742x only require two external bypass capacitors to operate.

9.2.2 Detailed Design Procedure

9.2.2.1 Maximum Supply Current Equations

(Calculated over recommended operating temperature range and Silicon process variation)

9.2.2.1.1 ISO7420

At $V_{CC1} = V_{CC2} = 3.3V \pm 10\%$

$$I_{CC1}(\text{max}) = I_{CC1_Q}(\text{max}) + 1.791 \times 10^{-2} \times f \quad (1)$$

$$I_{CC2}(\text{max}) = I_{CC2_Q}(\text{max}) + 1.687 \times 10^{-2} \times f + 3.570 \times 10^{-3} \times f \times C_L \quad (2)$$

At $V_{CC1} = V_{CC2} = 5V \pm 10\%$

$$I_{CC1}(\text{max}) = I_{CC1_Q}(\text{max}) + 3.152 \times 10^{-2} \times f \quad (3)$$

$$I_{CC2}(\text{max}) = I_{CC2_Q}(\text{max}) + 2.709 \times 10^{-2} \times f + 5.365 \times 10^{-3} \times f \times C_L \quad (4)$$

9.2.2.1.2 ISO7421

At $V_{CC1} = V_{CC2} = 3.3V \pm 10\%$

$$I_{CC1}(\text{max}) = I_{CC1_Q}(\text{max}) + 1.726 \times 10^{-2} \times f + 1.785 \times 10^{-3} \times f \times C_L \quad (5)$$

$$I_{CC2}(\text{max}) = I_{CC2_Q}(\text{max}) + 1.726 \times 10^{-2} \times f + 1.785 \times 10^{-3} \times f \times C_L \quad (6)$$

At $V_{CC1} = V_{CC2} = 5V \pm 10\%$

$$I_{CC1}(\text{max}) = I_{CC1_Q}(\text{max}) + 2.920 \times 10^{-2} \times f + 2.682 \times 10^{-3} \times f \times C_L \quad (7)$$

$$I_{CC2}(\text{max}) = I_{CC2_Q}(\text{max}) + 2.920 \times 10^{-2} \times f + 2.682 \times 10^{-3} \times f \times C_L \quad (8)$$

$I_{CC1_Q}(\text{max})$ and $I_{CC2_Q}(\text{max})$ are equivalent to the maximum supply currents measured in mA under DC input conditions (provided in the specification tables of this data sheet); f is data rate in Mbps of both channels; C_L is the capacitive load in pF of both channels. $I_{CC1}(\text{max})$ and $I_{CC2}(\text{max})$ are measured in mA.

9.2.2.2 Typical Supply Current Equations:

(Calculated over recommended operating temperature range and Silicon process variation)

9.2.2.2.1 ISO7420

At $V_{CC1} = V_{CC2} = 3.3V$

$$I_{CC1}(\text{typ}) = I_{CC1_Q}(\text{typ}) + 1.528 \times 10^{-2} \times f \quad (9)$$

$$I_{CC2}(\text{typ}) = I_{CC2_Q}(\text{typ}) + 1.637 \times 10^{-2} \times f + 3.275 \times 10^{-3} \times f \times C_L \quad (10)$$

At $V_{CC1} = V_{CC2} = 5V$

$$I_{CC1}(\text{typ}) = I_{CC1_Q}(\text{typ}) + 2.640 \times 10^{-2} \times f \quad (11)$$

$$I_{CC2}(\text{typ}) = I_{CC2_Q}(\text{typ}) + 2.502 \times 10^{-2} \times f + 4.919 \times 10^{-3} \times f \times C_L \quad (12)$$

9.2.2.2.2 ISO7421

At $V_{CC1} = V_{CC2} = 3.3V$

$$I_{CC1}(\text{typ}) = I_{CC1_Q}(\text{typ}) + 1.567 \times 10^{-2} \times f + 1.640 \times 10^{-3} \times f \times C_L \quad (13)$$

$$I_{CC2}(\text{typ}) = I_{CC2_Q}(\text{typ}) + 1.567 \times 10^{-2} \times f + 1.640 \times 10^{-3} \times f \times C_L \quad (14)$$

At $V_{CC1} = V_{CC2} = 5V$

$$I_{CC1}(\text{typ}) = I_{CC1_Q}(\text{typ}) + 2.550 \times 10^{-2} \times f + 2.416 \times 10^{-3} \times f \times C_L \quad (15)$$

$$I_{CC2}(\text{typ}) = I_{CC2_Q}(\text{typ}) + 2.550 \times 10^{-2} \times f + 2.461 \times 10^{-3} \times f \times C_L \quad (16)$$

Typical Application (continued)

I_{CC1_Q} (typ) and I_{CC2_Q} (typ) are equivalent to the typical supply currents measured in mA under DC input conditions (provided in the specification tables of this data sheet); f is data rate in Mbps of each channel; C_L is the capacitive load in pF of each channel. $I_{CC1}(\text{typ})$ and $I_{CC2}(\text{typ})$ are measured in mA.

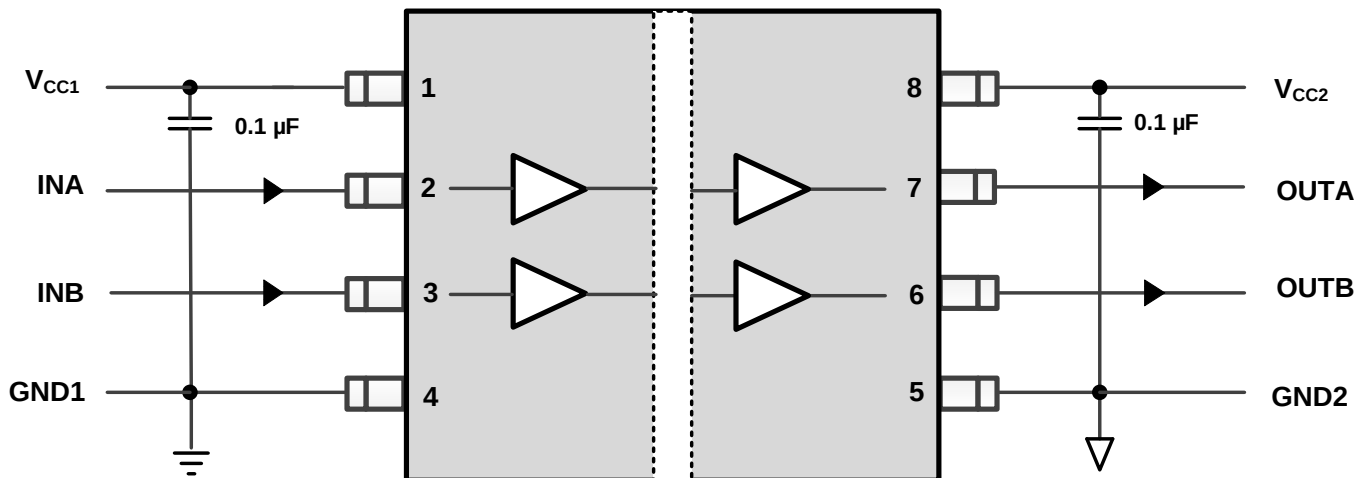


Figure 24. Typical ISO7420 Circuit Hookup

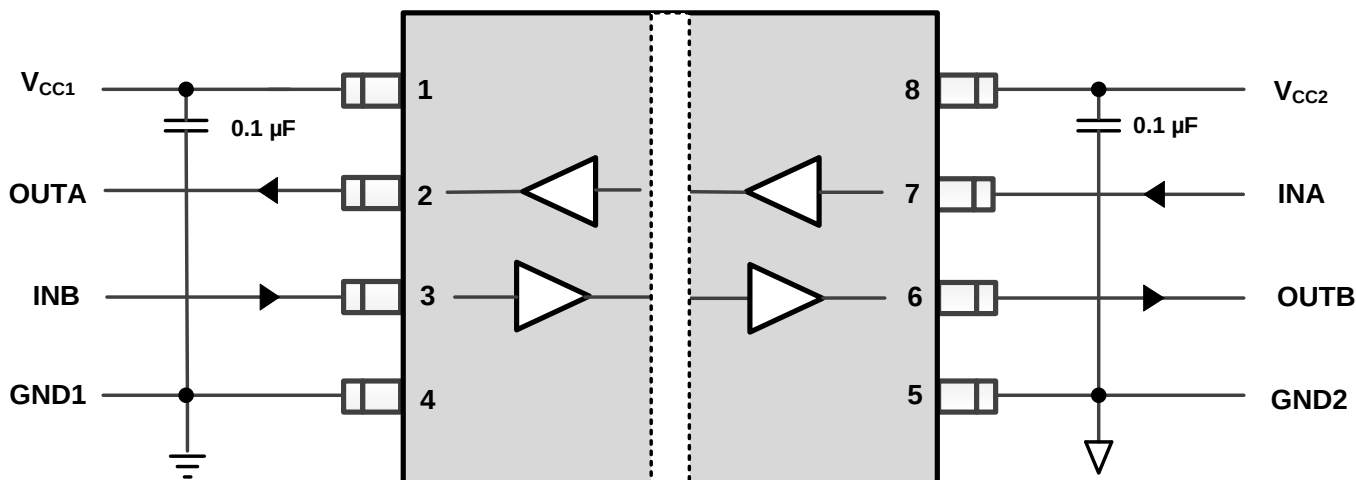


Figure 25. Typical ISO7421 Circuit Hookup

Typical Application (continued)

9.2.3 Application Curves

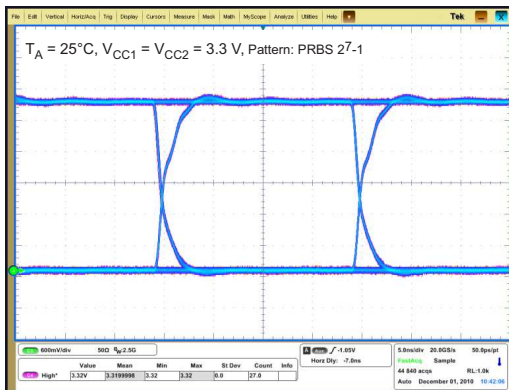


Figure 26. ISO7420FE Typical Eye Diagram at 50 MBPS, 3.3 V Operation

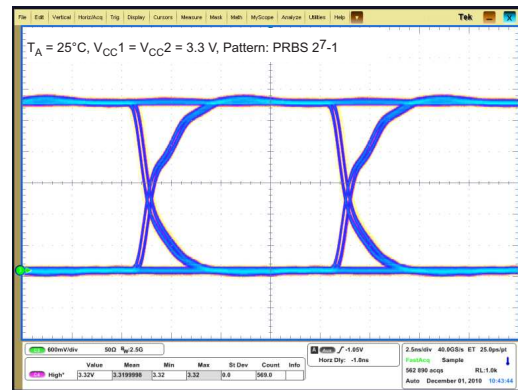


Figure 27. ISO7420FE Typical Eye Diagram at 100 MBPS, 3.3 V Operation

10 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, a 0.1 μF bypass capacitor is recommended at input and output supply pins (V_{CC1} and V_{CC2}). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' [SN6501](#). For such applications, detailed power supply design and transformer selection recommendations are available in [SN6501](#) datasheet ([SLLSEA0](#)).

11 Layout

11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 28](#)). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100pF/in².
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power / ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, see Application Note *Digital Isolator Design Guide*, [SLLA284](#).

11.1.1 PCB Material

For digital circuit boards operating below 150 Mbps, (or rise and fall times higher than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 epoxy-glass as PCB material. FR-4 (Flame Retardant 4) meets the requirements of Underwriters Laboratories UL94-V0, and is preferred over cheaper alternatives due to its lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and its self-extinguishing flammability-characteristics.

11.2 Layout Example

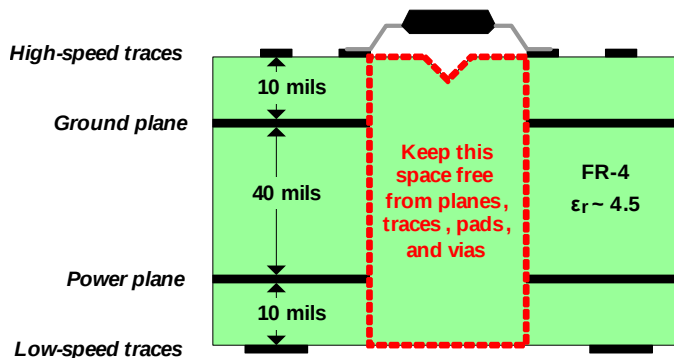


Figure 28. Recommended Layer Stack

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

相关文档如下：

- 《SN6501 用于隔离电源的变压器驱动器》， [SLLSEA0](#)
- 《隔离相关术语》， [SLLS353](#)

12.2 相关链接

以下表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，并且可以快速访问样片或购买链接。

表 3. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
ISO7420E	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISO7420FE	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISO7421E	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISO7421FE	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

12.3 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](#), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 商标

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12.5 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISO7420ED	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7420
ISO7420ED.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7420
ISO7420ED.B	Active	Production	SOIC (D) 8	75 TUBE	-	Call TI	Call TI	-40 to 125	
ISO7420EDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7420
ISO7420EDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7420
ISO7420EDR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
ISO7420FED	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420F
ISO7420FED.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420F
ISO7420FED.B	Active	Production	SOIC (D) 8	75 TUBE	-	Call TI	Call TI	-40 to 125	
ISO7420FEDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420F
ISO7420FEDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420F
ISO7420FEDR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
ISO7420FEDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420F
ISO7420FEDRG4.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420F
ISO7420FEDRG4.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
ISO7421ED	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7421
ISO7421ED.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7421
ISO7421ED.B	Active	Production	SOIC (D) 8	75 TUBE	-	Call TI	Call TI	-40 to 125	
ISO7421EDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7421
ISO7421EDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	SO7421
ISO7421EDR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
ISO7421FED	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7421F
ISO7421FED.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7421F
ISO7421FED.B	Active	Production	SOIC (D) 8	75 TUBE	-	Call TI	Call TI	-40 to 125	
ISO7421FEDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7421F
ISO7421FEDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	FULL NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7421F
ISO7421FEDR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) RoHS values: Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF ISO7421E :

- Automotive : [ISO7421E-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7420EDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7420FEDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7420FEDRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7421EDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7421FEDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



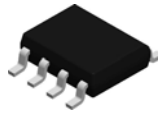
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7420EDR	SOIC	D	8	2500	350.0	350.0	43.0
ISO7420FEDR	SOIC	D	8	2500	350.0	350.0	43.0
ISO7420FEDRG4	SOIC	D	8	2500	350.0	350.0	43.0
ISO7421EDR	SOIC	D	8	2500	350.0	350.0	43.0
ISO7421FEDR	SOIC	D	8	2500	350.0	350.0	43.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
ISO7420ED	D	SOIC	8	75	505.46	6.76	3810	4
ISO7420ED.A	D	SOIC	8	75	505.46	6.76	3810	4
ISO7420FED	D	SOIC	8	75	505.46	6.76	3810	4
ISO7420FED.A	D	SOIC	8	75	505.46	6.76	3810	4
ISO7421ED	D	SOIC	8	75	505.46	6.76	3810	4
ISO7421ED.A	D	SOIC	8	75	505.46	6.76	3810	4
ISO7421FED	D	SOIC	8	75	505.46	6.76	3810	4
ISO7421FED.A	D	SOIC	8	75	505.46	6.76	3810	4

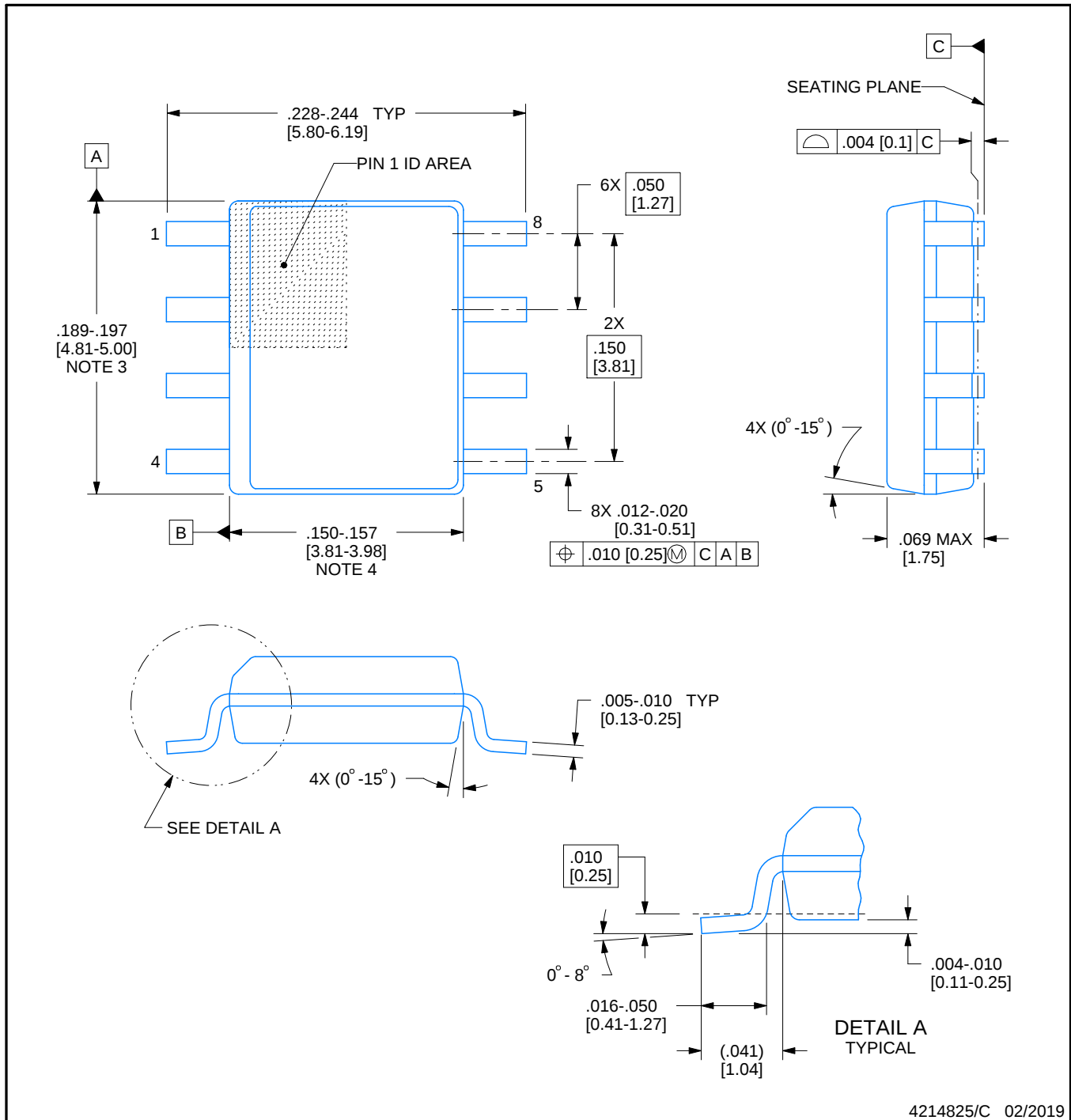


D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

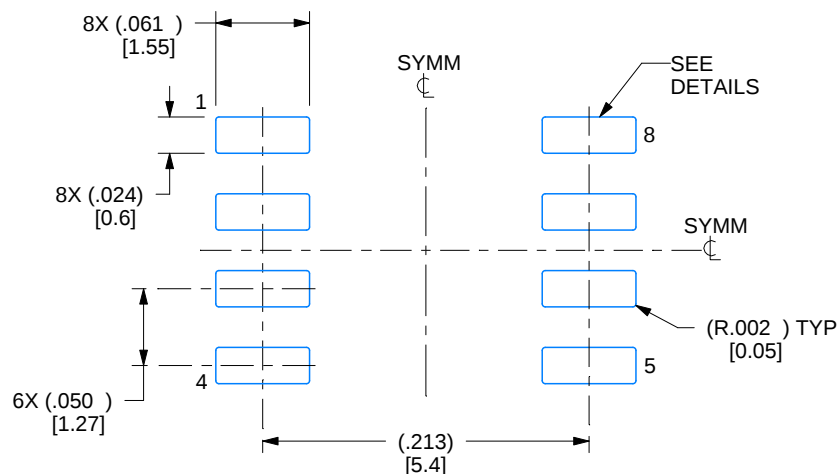
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

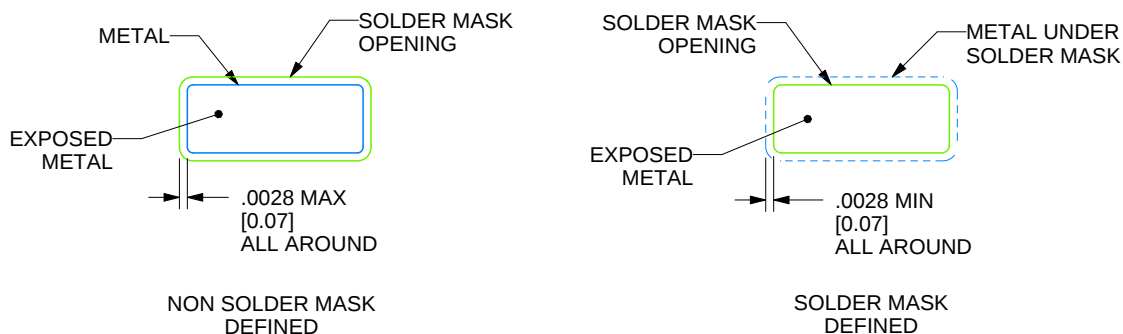
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

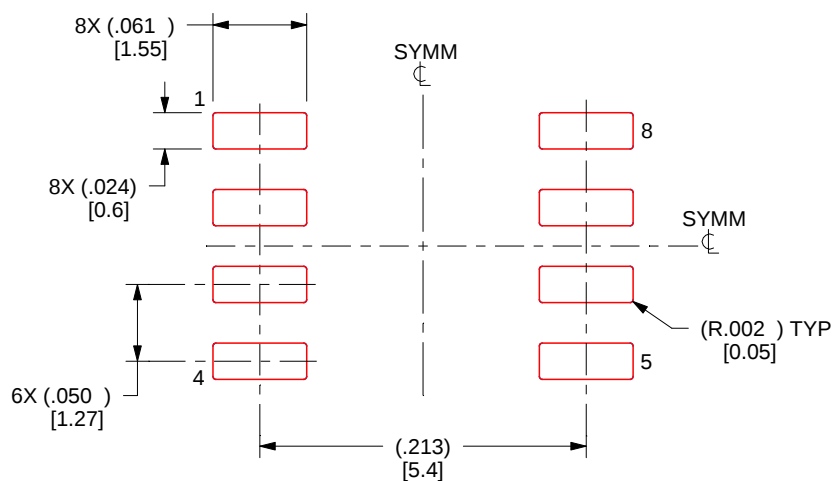
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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